

# 2SK3924-01L,S,SJ

## N-CHANNEL SILICON POWER MOSFET

■ Outline Drawings (mm) 200406

### FUJI POWER MOSFET Super FAP-G Series

#### ■ Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

#### ■ Applications

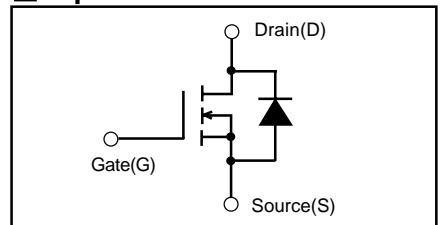
- Switching regulators
- DC-DC converters
- UPS (Uninterruptible Power Supply)

#### ■ Maximum ratings and characteristic

##### ● Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	250	V	
	V <sub>D SX</sub>	220	V	V <sub>GS</sub> =-30V
Continuous Drain Current	I <sub>D</sub>	14	A	
Pulsed Drain Current	I <sub>D(puls)</sub>	±56	A	
Gate-Source Voltage	V <sub>GS</sub>	±30	V	
Maximum Avalanche current	I <sub>AR</sub>	14	A	Note *1
Non-Repetitive Maximum Avalanche Energy	E <sub>AS</sub>	301.1	mJ	Note *2
Repetitive Maximum Avalanche Energy	E <sub>AR</sub>	10.5	mJ	Note *3
Maximum Drain-Source dV/dt	dV <sub>DS</sub> /dt	20	kV/μs	V <sub>DS</sub> ≤250V
Peak Diode Recovery dV/dt	dV/dt	5	kV/μs	Note *4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note *5
Max. Power Dissipation	P <sub>D</sub>	105	W	T <sub>c</sub> =25°C
		1.67		T <sub>a</sub> =25°C
Operating and Storage Temperature range	T <sub>ch</sub>	+150	°C	
	T <sub>stg</sub>	-55 to +150	°C	

#### ■ Equivalent circuit schematic



Note \*1: T<sub>ch</sub> ≤ 150°C, Repetitive and Non-repetitive

Note \*2: Starting T<sub>ch</sub>=25°C, I<sub>AS</sub>=6A, L=14.1mH,

V<sub>CC</sub>=48V, R<sub>G</sub>=50Ω

E<sub>AS</sub> limited by maximum channel temperature and Avalanche current.

See to the 'Avalanche Energy' graph

Note \*3: Repetitive rating: Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

Note \*4: I<sub>F</sub> ≤ -I<sub>D</sub>, -di/dt=100A/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C

Note \*5: I<sub>F</sub> ≤ -I<sub>D</sub>, dv/dt=5kV/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C

##### ● Electrical characteristics (Tc = 25°C unless otherwise specified)

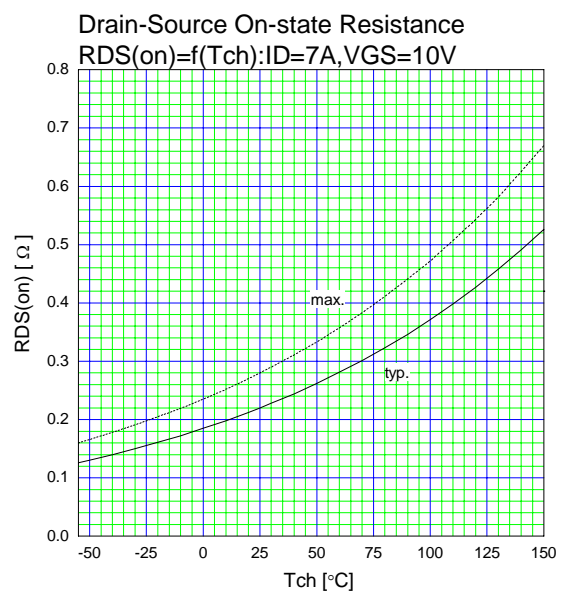
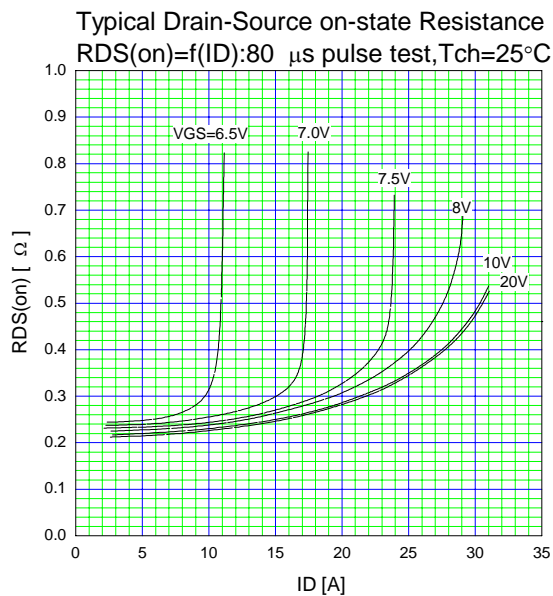
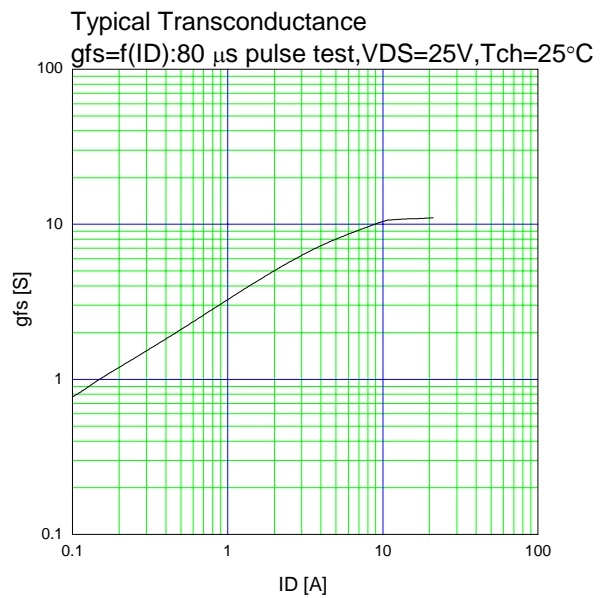
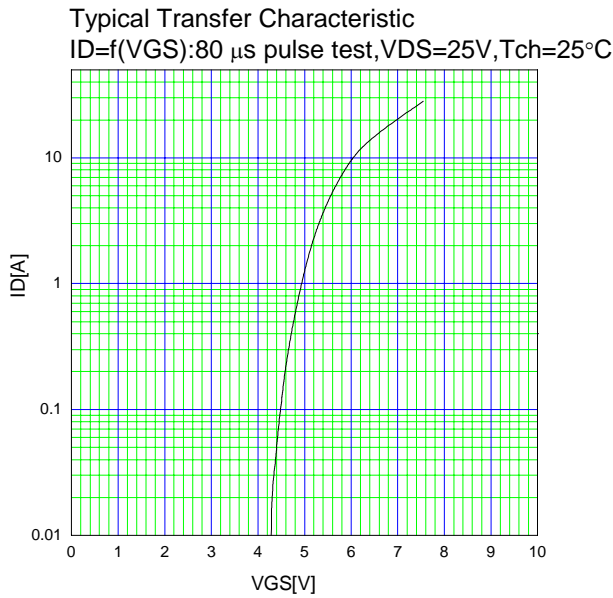
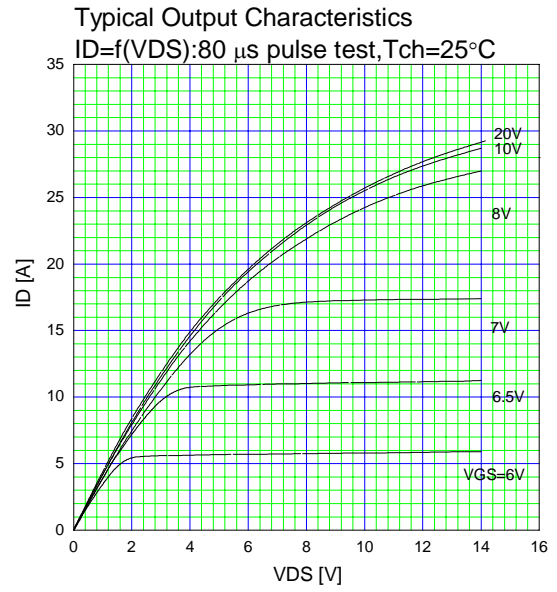
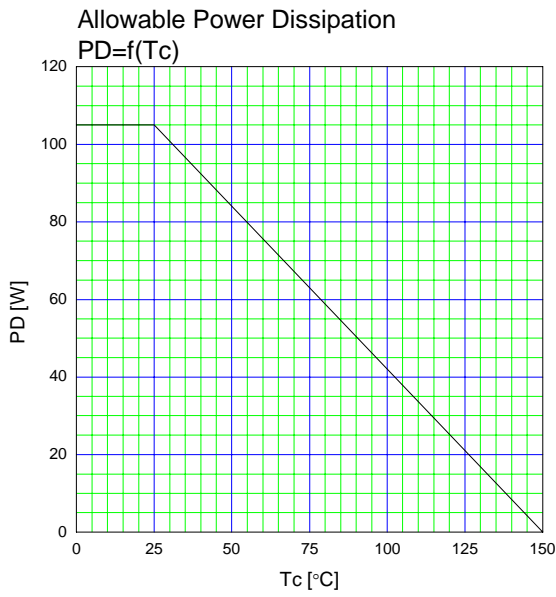
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA V <sub>GS</sub> =0V	250			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =250V V <sub>GS</sub> =0V			25	μA
		V <sub>DS</sub> =200V V <sub>GS</sub> =0V			2.0	mA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V			100	nA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =7A V <sub>GS</sub> =10V		220	280	mΩ
Forward Transconductance	g <sub>fs</sub>	I <sub>D</sub> =7A V <sub>DS</sub> =25V	5	10		S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =75V		780	1170	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		90	135	
Reverse Transfer Capacitance	C <sub>rss</sub>	f=1MH		6.0	9.0	
Turn-On Time t <sub>on</sub>	td(on)	V <sub>CC</sub> =48V I <sub>D</sub> =7A		12	18	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V		3	4.5	
Turn-Off Time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10Ω		23	35	
	t <sub>f</sub>			6	9	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =125V		22	33	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =14A		7.0	11	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		6.0	9.0	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =14A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.00	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =14A V <sub>GS</sub> =0V		120	250	ns
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		0.5	1.25	μC

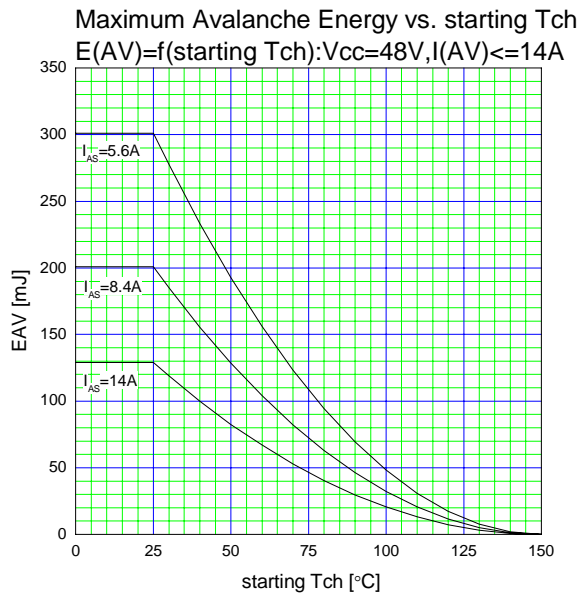
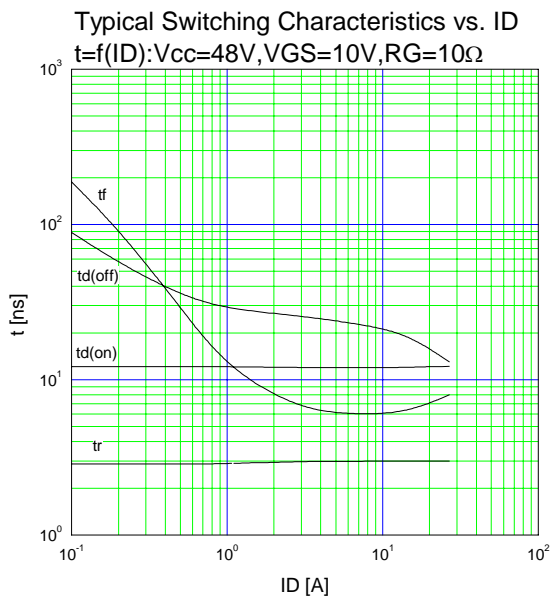
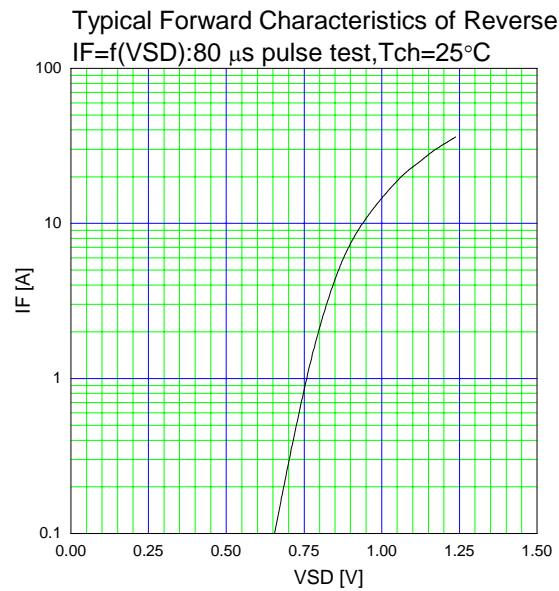
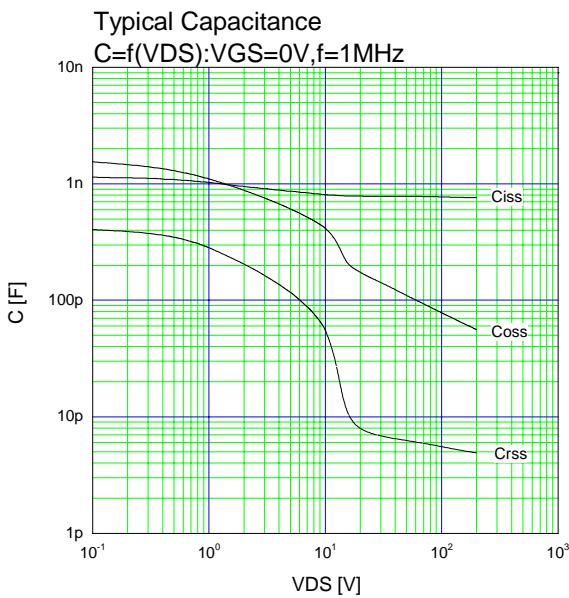
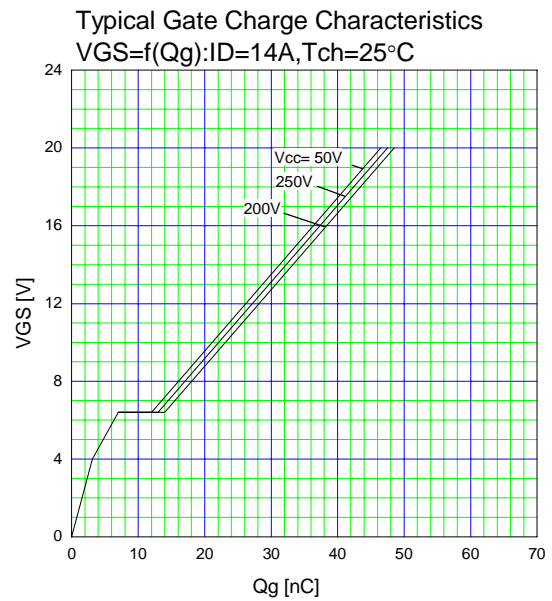
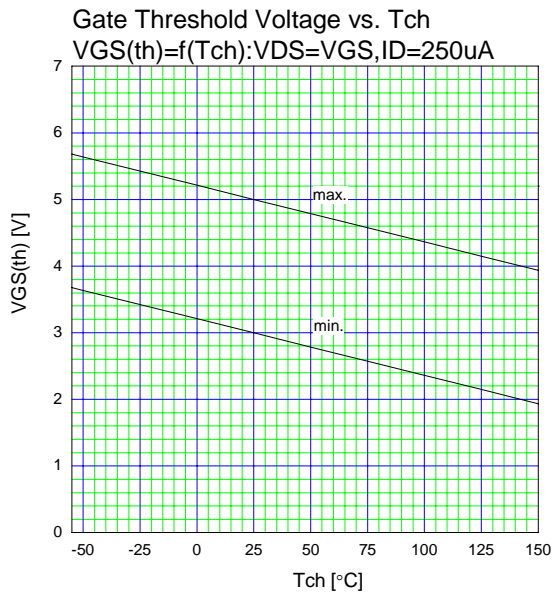
##### ● Thermal characteristics

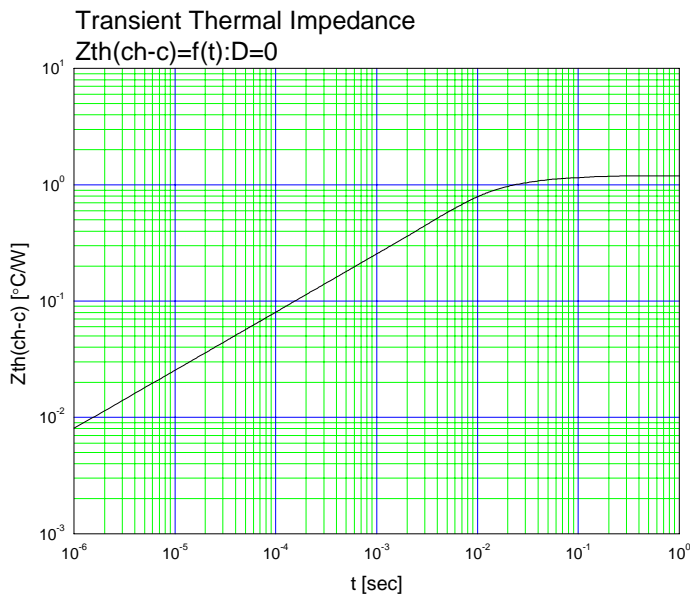
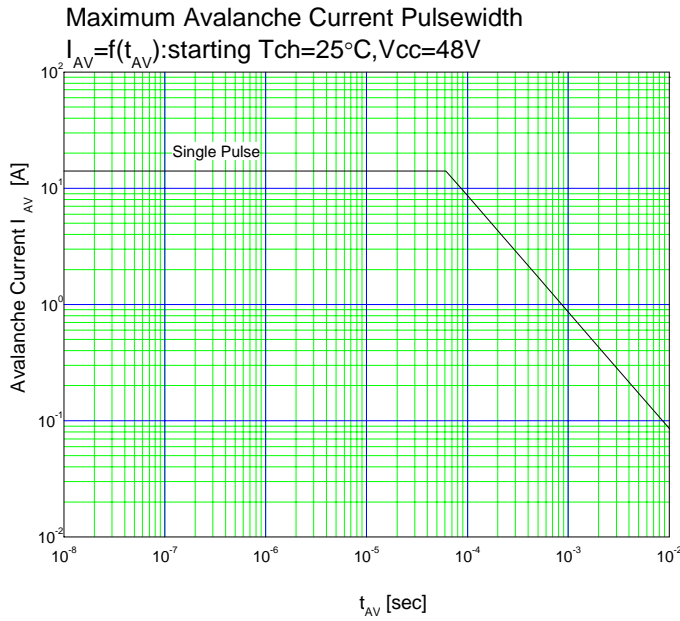
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			1.191	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			75	°C/W

See to P4

## Characteristics







## Outline Drawings (mm)

